Atty Docket No. Application No.: UNTYP018 10/612,776 Information Disclosure Applicant: Statement By Applicant (Use Several Sheets if Necessary) Atty Docket No. Application No.: 10/612,776 Applicant: Group July 1, 2003 2824

U.S. Patent Documents

Examiner						Sub-	Filing
Initial	No.	Patent No.	Date	Patentee	Class	class	Date
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.gen	L	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications", Applied Physics Letters, Vol. 77, No. 1, 3 July 2000,139-141.		
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified) Information Disclosure

Statement By Applicant

(Use Several Sheets if Necessary)

Atty Docket No.	Application No.:
UNTYP018	10/612,776
Applicant:	
Rinerson et al.	
Filing Date	Group
July 1, 2003	2824

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